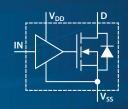
eGaN® IC DATASHEET EPC21601

# **EPC21601** – eToF™ Laser Driver IC

40 V 15 A Peak







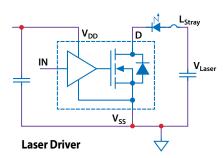


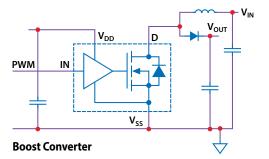
The EPC21601 is a laser driver that is controlled using 3.3 V logic at high frequencies of up to 100 MHz to modulate laser driving currents of up to 15 Amps. Full driver integration is achieved using EPC's proprietary GaN IC technology.

Wafer-level chip-scale packaging is used resulting in a BGA package that measures only 1.5 x 1 mm. The BGA package has low inductance and lays out very well with the laser system.

The EPC21601 uses a 5 V logic supply and is capable of interfacing to digital controllers. It can switch at frequencies exceeding 100 MHz.

**Figure 1: Typical Connection Diagrams** 





# **Absolute Maximum Ratings**

Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to  $V_{SS}$  unless indicated otherwise.

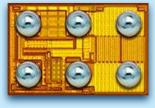
Symbol	Definition	MIN	MAX	UNIT
V <sub>D</sub>	Drain Voltage		40	
$V_{DD}$	Logic Supply Voltage	-0.3	5.5	V
IN	Logic Input	-0.3	5	
I <sub>D</sub>	Average Drain Current		3.4	Α
TJ	Operating Junction Temperature	-40	125	°C
T <sub>STG</sub>	Storage Temperature	-40	150	

## **ESD Ratings**

Symbol	Definition	MIN	UNIT
HBW	Human-body model	+/-250	W
CDM	Charged-device model <sup>6</sup>	N/A	V

## **Thermal Characteristics**

Symbol	Definition		UNIT
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	5.7	
$R_{\theta JB}$	Thermal Resistance, Junction-to-Board	23	0C // //
R <sub>RθJA_JEDEC</sub>	Thermal Resistance, Junction-to-Ambient (using JEDEC 51-2 PCB)	130	°C/W
R <sub>θJA _EVB</sub>	Thermal Resistance, Junction-to-Ambient (using EPC9154 EVB)	120	



Die size: 1.5 x 1 mm

**EPC21601** eGaN® FETs are supplied in passivated die form with solder bumps.

#### Features

- V<sub>Laser</sub> operating range up to 30 V
- 15 Amp peak current
- Switching frequency greater than 100 MHz
- Typical voltage switching time 750 ps
- 5 V nominal logic power supply
- 3.3 V logic compatible input control
- 1.5 ns minimum output pulse width
- 3.5 ns delay time from input to output

### **Applications**

- · Time of flight measurement
  - Gesture recognition
  - Gaming
  - Driver monitoring
  - Robotic vision
  - Industrial safety
- ToF module using VCEL laser for camera modules, laptops and smart phones
- · Boost control switch
- · Flyback control switch
- Forward control switch
- · Class-E Amplifier

Scan QR code or click link below for more information including reliability reports, device models, demo boards!



https://l.ead.me/EPC21601

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# **Recommended Operating Conditions**

For proper operation the device should be used within the recommended conditions. All voltage parameters are absolute voltages referenced to V<sub>SS</sub> unless indicated otherwise.

Symbol	Definition	MIN	ТҮР	MAX	UNIT
V <sub>Laser</sub>	Laser Driver Voltage <sup>5</sup>	5		30	V
V <sub>DD</sub>	Logic Supply Voltage <sup>5</sup>		5		V

## **Truth Table**

IN	Laser
0	Off
1	On

## **Electrical Characteristics**

All ratings at  $T_J$  = 25 °C.  $V_{Laser}$  = 20 V,  $I_D$  = 10 A,  $V_{IL}$  = 0 V,  $V_{IH}$  = 3.3 V,  $V_{DD}$  = 5 V, unless indicated otherwise.

Symbol	Definition	MIN	TYP	MAX	UNIT
Operating	Power Supply, V <sub>DD</sub>				
I <sub>DD (Off)</sub>	V <sub>DD</sub> Quiescent current with laser driver off		11	20	
I <sub>DD (30 MHz)</sub>	Operating current off V <sub>DD</sub> at 30 MHz		50	70	mA
Input Pins					
V <sub>IH</sub>	High-level input voltage	1.9			.,
V <sub>IL</sub>	Low-level input voltage			0.5	V
V <sub>IHyst</sub>	Hysteresis between rising and falling threshold	53			mV
R <sub>IN</sub>	Input pulldown resistance		1.25		kΩ
Power Sta	ge			'	
R <sub>DS(on)</sub> <sup>1</sup>	Drain to Source Resistance		40		mΩ
I <sub>D(peak)</sub> 1	Peak Laser Drive Current Capability, f = 50 MHz	15			Α
C <sub>OSS</sub> <sup>1</sup>	$V_{DS} = 20 \text{ V}, V_{IN} = 0 \text{ V}$		49		рF
Q <sub>OSS</sub> <sup>1</sup>	$V_{DS} = 20 \text{ V}, V_{IN} = 0 \text{ V}$		1.5		nC
E <sub>OSS</sub> <sup>1</sup>	$V_{DS} = 20 \text{ V}, V_{IN} = 0 \text{ V}$		13		nJ
C <sub>OSS(ER)</sub> 1,2	$V_{DS} = 0$ to 20 V, $V_{IN} = 0$ V		63		
C <sub>OSS(TR)</sub> 1,3	V <sub>DS</sub> = 0 to 20 V, V <sub>IN</sub> = 0 V		73		pF
	Characteristics	•			
t <sub>D(on)</sub> 1	Turn on delay time		3.5	6.75	
$t_F^{-1}$	Drain fall time		0.75	1.5	
t <sub>D(off)</sub> 1	Turn off delay time		3.2	5.5	
t <sub>R</sub> 1,4	Drain rise time		0.32		
t <sub>dPW</sub> 1	Pulse width distortion	- 2	-0.24	1.6	ns
t <sub>in(min(on))</sub> 1	Minimum input pulse width		2.5		
t <sub>D(min(on))</sub> 1	Minimum drain pulse width		1.5		
t <sub>On(Max)</sub> 1	Maximum on time		500		
f <sub>Max</sub> 1	Maximum frequency, 0 °C to 100 °C		100		MHz

# **Pinout Description**

Pin	Description		
V <sub>DD</sub>	Input Voltage Supply (Decouple to $V_{SS}$ with small, low inductance capacitor)		
IN	Logic input		
D	Power Drain		
V <sub>SS</sub>	Power and Signal Return		

### **Notes:**

- 1. Guaranteed by design, but not tested
- 2.  $C_{OSS(ER)}$  is a fixed capacitance that gives the same stored energy as  $C_{OSS}$  while  $V_{DS}$  is rising from 0 to 50%  $BV_{DSS}$
- 3.  $C_{OSS(TR)}$  is a fixed capacitance that gives the same charging time as  $C_{OSS}$  while  $V_{DS}$  is rising from 0 to 50%  $BV_{DSS}$
- 4. Drain rise time is determined by ZVS charging of the output capacitance
- 5. See Power Sequencing section in Applications Information for considerations on laser drive voltage
- 6. Paragraph 2.7 of AEC Q100-011 Rev. D, Jan. 29, 2019 states that CDM specification is not necessary on such a small device.

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## **Performance Curves**

Figure 2: Typical Quiescent Current vs. Frequency

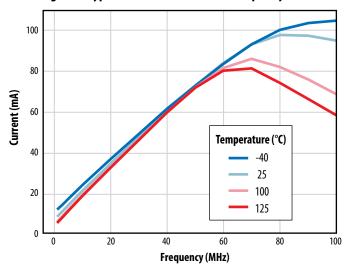


Figure 3: Typical Quiescent Current vs. Temperature

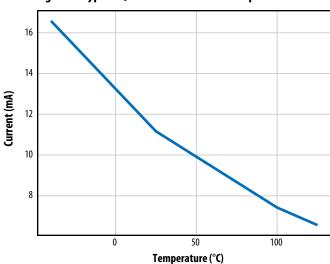


Figure 4: Turn On Propagation Delay vs. Temperature

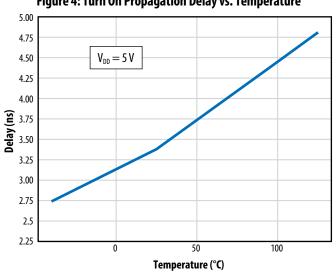


Figure 5: Turn Off Propagation Delay vs. Temperature

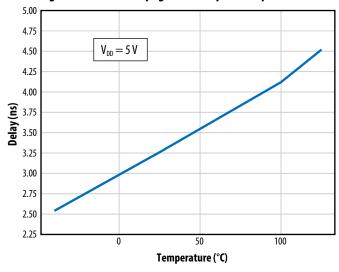


Figure 6: Typical Coss

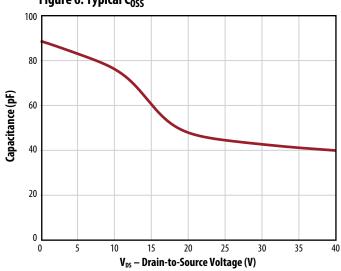
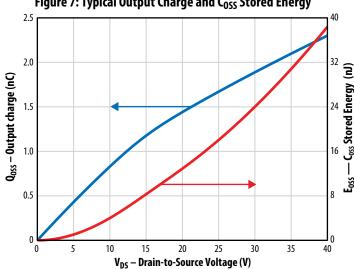
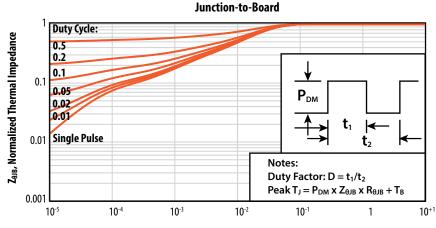


Figure 7: Typical Output Charge and Coss Stored Energy

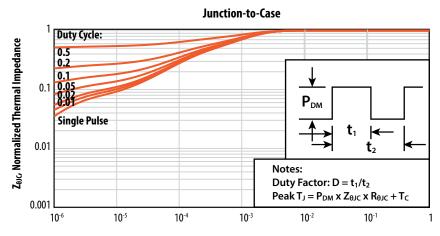


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**Figure 8: Transient Thermal Impedance** 



t<sub>1</sub>, Rectangular Pulse Duration, seconds



t<sub>1</sub>, Rectangular Pulse Duration, seconds

# **Application Information**

## **Safety Warning**

This device is capable of driving laser diodes to generate high power optical pulses. Such pulses are capable of causing **PERMANENT VISION DAMAGE AND BLINDNESS** as well as additional injury or property damage. Laser diodes may emit infrared (IR) light that is invisible to the user, but which can still cause **PERMANENT VISION DAMAGE AND BLINDNESS** as well as additional injury or property damage. User is fully responsible for following proper laser safety procedures to prevent injury or damage.

## **Power Sequencing**

IN must be held low during power up sequence. For power up,  $V_{DD}$  must be applied before applying voltage to the drain to prevent possible unwanted turn on of the output. For power down, the order must be reversed.

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Power Up	IN	V <sub>DD</sub>	Drain
1	Low	0 V	0 V
2	Low	5 V	0 V
3	Low	5 V	V <sub>Laser Drive</sub>
4	Active	5 V	V <sub>Laser Drive</sub>
Power Down	IN	V <sub>DD</sub>	Drain
1	Low	5 V	V <sub>Laser Drive</sub>
2	Low	5 V	0 V
3	Low	0 V	0 V

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# **Application Information** (continued)

# Layout and decoupling

Minimizing inductance in both power and gate drive loops is critical. The power loop is primary, and gate drive loop secondary. Short, wide traces are required, and returning in the second layer, using a thin dielectric will cancel much of the inductance. Using multiple ceramic capacitors in parallel will reduce stray inductance and impedance in the power loop. Use high quality NPO or COG capacitors for both power and gate drive. This will increase effective capacitance as capacitors with lower quality materials will lose much more capacitance with voltage. Recommended layout is shown below. Component recommendations for power and gate drive decoupling capacitors are shown in the EPC9154 demonstration board quick start guide.

Turn off current is limited by the energy of the power loop stray inductance transferring to the  $C_{\mbox{\scriptsize OSS}}$  of the power FET of the laser driver.  $E_{OSS}$  vs.  $V_{DS}$  curve is in the datasheet.

#### Start up

V<sub>DD</sub> should be applied before the laser voltage. For applications where the laser voltage is below 10 V and at elevated temperatures, it may take a few pulses before the pulse width stabilizes.

## **Output Capacitance**

Output capacitance (Coss) is the capacitance between drain and ground. Output charge ( $Q_{OSS}$ ) is the integral of output capacitance over voltage. Just like discrete power FETs, output capacitance is charged and discharged with each cycle. This takes time and dissipates power. Please refer to FET application notes to determine impact.

Figure 9: Power and Gate Drive Turn On Loops

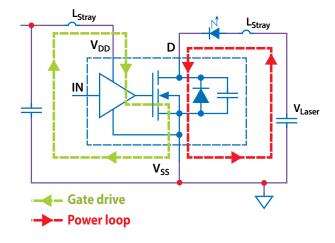
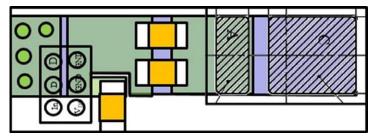


Figure 10: Recommended Layout



Cathode to drain connection on second conductor layer

Figure 11: Parameter Measurement Test Circuits

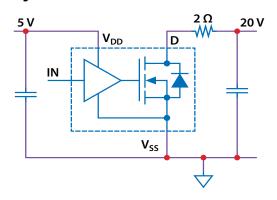
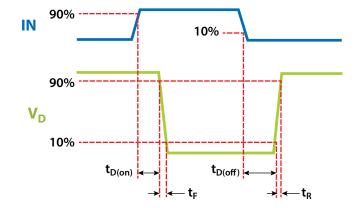


Figure 12: Parameter Measurement Definitions

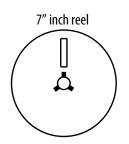


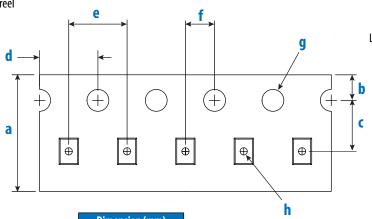
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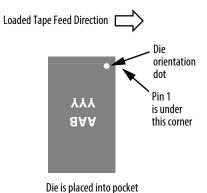
## **TAPE AND REEL CONFIGURATION**

• 4 mm pitch, 8 mm wide tape on 7" reel

• Standard reel packages 2,500 units





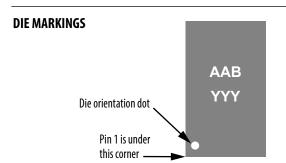


solder bump side down (face side down)

	Dimension (mm)		
<b>EPC21601 (Note 1)</b>	Target	MIN	MAX
a	8.00	7.90	8.30
b	1.75	1.65	1.85
<b>c</b> (Note 2)	3.50	3.45	3.55
d	4.00	3.90	4.10
е	4.00	3.90	4.10
f (Note 2)	2.00	1.95	2.05
g	1.50	1.50	1.60
h	0.50	0.45	0.55

Note 1: MSL 1 (moisture sensitivity level 1) classified according to IPC/ JEDEC industry standard.

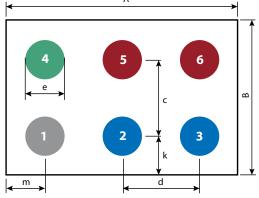
Note 2: Pocket position is relative to the sprocket hole measured as true position of the pocket, not the pocket hole.



Dove	Laser M	arkings
Part Number	Lot_Date Code Marking Line 1	Lot_Date Code Marking Line 2
EPC21601	AAB	YYY

## **DIE OUTLINE**

Solder Bump View



d →	
	518 ±25
Seating plane	200 ±20 A

DIM		MICROMETERS	
DIM	MIN	Nominal	MAX
Α	1420	1450	1480
В	920	950	980
C		500	
d		500	
e	238	264	290
k		225	
m		225	

Pad 1 is IN;

Pads 2 & 3 are Drain;

Pad 4 is V<sub>DD</sub>;

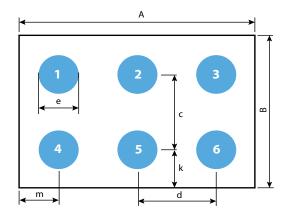
Pads 5 & 6 are V<sub>ss</sub>

Side View

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# RECOMMENDED LAND PATTERN

(units in  $\mu$ m)



DIM	MICROMETERS
Α	1450
В	950
c	500
d	500
e	230
k	225
m	225

Pad 1 is IN;

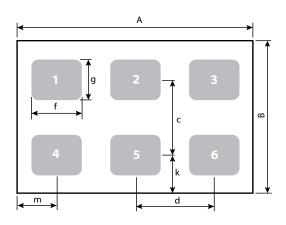
Pads 2 & 3 are Drain;

Pad 4 is V<sub>DD</sub>;

Pads 5 & 6 are V<sub>SS</sub>

# RECOMMENDED STENCIL DRAWING

(measurements in µm)



DIM	MICROMETERS
Α	1450
В	950
c	500
d	500
f	300
g	250
k	225
m	225

Recommended stencil should be 4mil (100  $\mu$ m) thick, must be laser cut, opening per drawing.

The corner has a radius of R60

Intended for use with SAC305 Type 4 solder, reference 88.5% metals content.

Additional assembly resources available at

https://epc-co.com/epc/DesignSupport/AssemblyBasics.aspx

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